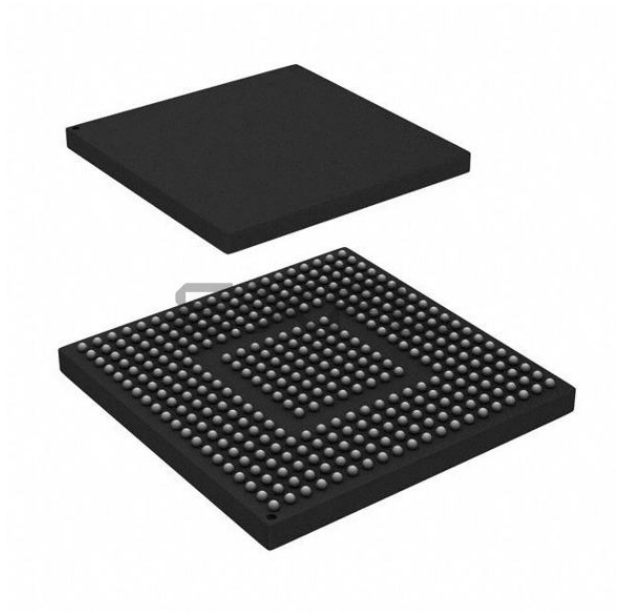

Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	ARM® Cortex®-A5 + Cortex®-M4
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	500MHz, 167MHz
Co-Processors/DSP	Multimedia; NEON™ MPE
RAM Controllers	LPDDR2, DDR3, DRAM
Graphics Acceleration	Yes
Display & Interface Controllers	DCU, GPU, LCD, VideoADC, VIU
Ethernet	10/100Mbps (2)
SATA	-
USB	USB 2.0 OTG + PHY (1)
Voltage - I/O	3.3V
Operating Temperature	-40°C ~ 85°C (TA)
Security Features	ARM TZ, CAAM, HAB, RTIC, Secure JTAG, SNVS, Tamper, TZ ASC, TZ WDOG
Package / Case	364-LFBGA
Supplier Device Package	364-LFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mvf61ns151cmk50

- Display and Video
  - Dual Display Control Unit (DCU) with support for color TFT display up to SVGA
  - Segmented LCD (3V Glass only) configurable as 40x4, 38x8, and 36x6
  - Video Interface Unit (VIU) for camera
  - Open VG Graphics Processing Unit (GPU)
  - VideoADC
- Analog
  - Dual 12-bit SAR ADC with 1MS/s
  - Dual 12-bit DAC
- Audio
  - Four Synchronous Audio Interface (SAI)
  - Enhanced Serial Audio Interface (ESAI)
  - Sony Philips Digital Interface (SPDIF), Rx and Tx
  - Asynchronous Sample Rate Converter (ASRC)
- Human-Machine Interface (HMI)
  - GPIO pins with interrupt support, DMA request capability, digital glitch filter.
  - Hysteresis and configurable pull up/down device on all input pins
  - Configurable slew rate and drive strength on all output pins
- On-Chip Memory
  - 512 KB On-chip SRAM with ECC
  - 1 MB On-chip graphics SRAM (no ECC). This depends on the part selected. Alternate configuration could be 512 KB graphics and 512 KB L2 cache.
  - 96 KB Boot ROM

Field	Description	Values
R	Revision	• 1 = Rev 1.x
T	Temperature range (°C)	• C = -40 °C to +85 °C T_a
PP	Package type	• KU = 176LQFP • MK = 364 MAPBGA
S	Speed	• Speed A5 Core • 26 = 266MHz • 40 = 400MHz • 50 = 500MHz

2.4 Part Numbers

This table lists the part numbers on the device.

Part Number	Package	Description
MVF30NN151CKU26	LQFP-EP 176 24*24*1.6	A5-266, No Security, 176LQFP
MVF30NS151CKU26	LQFP-EP 176 24*24*1.6	A5-266, Security, 176LQFP
MVF50NN151CMK40	MAP 364 17*17*1.5 P0.8	A5-400, No Security, 364BGA
MVF50NS151CMK40	MAP 364 17*17*1.5 P0.8	A5-400, Security, 364BGA
MVF50NN151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, No Security, 364BGA
MVF50NS151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, Security, 364BGA
MVF51NN151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, L2 Cache, No Security, 364BGA
MVF51NS151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, L2 Cache, Security, 364BGA
MVF60NN151CMK40	MAP 364 17*17*1.5 P0.8	A5-400, M4, No Security, 364BGA
MVF60NS151CMK40	MAP 364 17*17*1.5 P0.8	A5-400, M4, Security, 364BGA
MVF60NN151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, M4, No Security, 364BGA
MVF60NS151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, M4, Security, 364BGA
MVF61NN151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, M4, L2 Cache, No Security, 364BGA
MVF61NS151CMK50	MAP 364 17*17*1.5 P0.8	A5-500, M4, L2 Cache, Security, 364BGA
MVF62NN151CMK40	MAP 364 17*17*1.5 P0.8	A5-400, M4 Primary, No Security, 364BGA

Table 3. LPREG electrical characteristics (continued)

Parameters	Min	Typ	Max	Unit	Comments
PSRR with 4.7uF output cap					
@ DC @noload			-40	dB	
@ DC @full load			-35		
Worst case @ any frequency			-12		

6.2.1.3 ULPREG electrical characteristics

Table 4. ULPREG electrical characteristics

Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	
Current Consumption	1.88	2.3	2.86	µA	@ no load
	-	610	670	µA	@ full load
Output current capacity			20	mA	DC load current
Output voltage @ no load			1.175	V	
Output voltage @ full load	1.125			V	
PSRR with 500 pF output cap	-20			dB	Worst case at any frequency across corners
@ DC @noload			-50	dB	
@200KHz @noload			-37		
@ DC @full load			-42		
@200KHz @full load			-37		
Worst case @ any frequency @ any load			-15		

6.2.1.4 WBREG electrical characteristics

Table 5. WBREG electrical characteristics

Parameters	Min	Typ	Max	Unit	Comments
Power supply	3	3.3	3.6	V	-
Current Consumption	-	2	5	µA	@ no load
	-	2	5	µA	@ full load
Output current capacity	-	1	2	mA	DC load current
Output voltage @ no load		1.4	1.425	V	
Output voltage @ full load	1.375	1.398		V	
Output voltage programmability	1.4	1.4	1.7	V	16 steps of 25 mV each

6.2.3.3 LDO_3P0

Table 14. LDO_3P0 parameters

Specification	Min	Typ	Max	Unit	Comments
Input OTG VBUS Supply	4.4		5.25	V	
Input HOST VBUS Supply	4.4		5.25	V	
VDD3P0_OUT	2.9	3.0	3.1	V	Regulator output at default setting
I_out	-		50	mA	500 mV drop-out voltage
Regulator output programming range	2.625		3.4	V	Programmable in 25mV steps
[P:][C:] Brownout Voltage	2.75	2.85		V	
Brownout offset step	0	-	175	mV	Programmable in 25mV steps
Minimum external decoupling capacitor	1	-	-	µF	low ESR

NOTE

These values are with Anadig_REG_3P0[ENABLE_ILIMIT]= 0 and Anadig_REG_3P0[ENABLE_LINREG]= 1. It is required to set these values before using USB.

6.2.4 Power consumption operating behaviors

Table 15. Power consumption operating behaviors

Symbol	Description	Typ.[1]	Max.[2]	Unit	Notes
I_{DD_RUN}	Run mode current — All functionalities of the chip available	400	850	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.3 V ± 10%	80	500	mA	3
I_{DD_LPRUN}	Low-power run mode current at 3.3 V ± 10%, 24MHz operation, PLL Bypass.	13	325	mA	4
I_{DD_ULPRUN}	Ultra-low-power run mode current at 3.3 V ± 10%	12	395	mA	5
I_{DD_STOP}	Stop mode current at 3.3 V ± 10%	7	300	mA	6
I_{DD_LPS3}	Low-power stop3 mode current at 3.3 V ± 10%	300	1300	uA	7
I_{DD_LPS2}	Low-power stop 2 mode current at 3.3 V ± 10%	50	875	uA	8
I_{DD_VBAT}	Battery backup mode	5	45	uA	9

1. The Typ numbers represent the average value taken from a matrix lot of parts across normal process variation at ambient temperature.

2. The Max numbers represent the single worst case value taken from a matrix lot of parts across normal process variation at maximum temperature.
3. CA5, CM4 cores halted
4. 24MHz operation, PLL Bypass
5. 32 kHz /128 kHz operation, PLL Off
6. Lowest power mode with all power retained, RAM retention and LVD protection.
7. Standby Mode. 64K RAM retention. I/O states held. ADCs/DACs optionally power-gated. RTC functional. Wakeup from interrupts. Fast IRC enabled.
8. Standby Mode 16K RAM retention. I/O states held. ADCs/DACs optionally power-gated. RTC functional. Wakeup from interrupts. Fast IRC enabled.
9. All supplies OFF, SRTC, 32kXOSC ON, tampers and monitors ON. 128k IRC optionally ON.

6.2.5 USB PHY current consumption

6.2.5.1 Power Down Mode

Everything powered down, including the VBUS valid detectors, typ condition.

Table 16. USB PHY Current Consumption in Normal Mode

	USBx_VBUS (3.0V) Avg	VDD33_LDOIN (2.5V) Avg	VDD33_LDOIN (1.1V) Avg
Current	5.1 µA	1.7 µA	<0.5 µA

NOTE

The currents on the 2.5 voltage regulator and 3.0 voltage regulator were identified to be the voltage divider circuits in the USB-specific level shifters.

6.2.6 EMC radiated emissions operating behaviors

Table 17. EMC radiated emissions operating behaviors

Symbol	Condition[1]	Clocks	Frequency band [2]	Level (Typ)[3]	Unit
V_{EME}	Device Configuration, test conditions and EM testing per standard IEC 61967-2; Supply voltages: VDD= 5.0 V VDD33 = 3.3 V VDD15 = 1.5 V VDD12 = 1.2 V Temp = 25°C	FCPU = 396 MHz FBUS = 66 MHz External Crystal = 24 MHz	150 KHz – 50 MHz	22	dBµV
			50 MHz – 150 MHz	24	
			150 MHz – 500 MHz	25	
			500–1000	20	
			IEC level[4]	K	—

1. Measurements were made per IEC 61967-2 while the device was running basic application code.
2. Measurements were performed on the BGA364 version of the device

3. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
4. IEC Level Maximums: N ≤ 12dBmV, M ≤ 18dBmV, L ≤ 24dBmV, K ≤ 30dBmV, I ≤ 36dBmV, H ≤ 42dBmV

6.2.7 EMC Radiated Emissions Web Search Procedure boilerplate

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

6.2.8 Capacitance attributes

Table 18. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

7 I/O parameters

7.1 GPIO parameters

Table 19. GPIO DC operating conditions

Symbol	Parameter	Min	Typ	Max	Unit
vddi[1]	Core internal supply voltage		1.2		V
ovdd	I/O output supply voltage	3	3.3	3.6	V

1. This is internally controlled.

Table 20. GPIO DC Electrical characteristics

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
Voh	High-level output voltage	Ioh= -1mA	ovdd-0.15			V

Table continues on the next page...

Table 22. Output Buffer Average Impedance (3.3V power mode) (continued)

Symbol	Parameter	Drive strength[1]	Min	Typ	Max	Unit
		1 0 0	30	37	58	
		1 0 1	24	30	46	
		1 1 0 Extra drive strength	20	25	38	
		1 1 1	17	20	32	

1. The drive strengths are controlled by the DSE bit of the Software MUX Pad Control Register. For details, see IOMUX Controller chapter of the device reference manual.

7.2 DDR parameters

Table 23. DDR operating conditions

Symbol	Parameter	Min	Typ	Max	Unit
vddi	Core internal supply voltage	1.16	1.23	1.26	V
ovdd	I/O output supply voltage (DDR3 mode)	1.425	1.5	1.575	V
ovdd	I/O output supply voltage (LPDDR2 mode)	1.14	1.2	1.26	V
vdd2p5	I/O PD predriver and level shifters supply voltage	2.25	2.5	2.75	V

Table 24. LPDDR2 mode DC Electrical characteristics

Symbol	Parameter	Test condition	Min	Typ	Max	Unit	Notes
Voh	High-level output voltage		0.9*ovdd			V	Note that the JEDEC LPDDR2 specification (JESD209_2B) supersedes any specification in this document.
Vol	Low-level output voltage				0.1*ovdd	V	
Vref	Input reference voltage		0.49*ovdd	0.5*ovdd	0.51*ovdd	V	
Vih(dc)	DC input high voltage		Vref+0.13		ovdd	V	
Vil(dc)	DC input low voltage		ovss		Vref-0.13	V	
Vih(diff)	DC differential input logic high		0.26		Note[1]	V	
Vil(diff)	DC differential input logic low		Note[1]		-0.26	V	

Table continues on the next page...

Table 24. LPDDR2 mode DC Electrical characteristics (continued)

Symbol	Parameter	Test condition	Min	Typ	Max	Unit	Notes
Iin[2]	Input current (no pull-up/ down)	Vin = ovdd or 0			2.5	uA	
Tri-state I/O supply current[2]	Icc-ovdd	Vin = ovdd or 0			4		
Tri-state vdd2p5 supply current[2]	Icc-vdd2p5	Vi = vddi or 0			1.5		
Tri-state core supply current[2]	Icc-vddi				1		
Driver unit (240 Ohm) calibration resolution	Rres				10	Ohm	

1. The single-ended signals need to be within the respective limits (Vih(dc) max, Vil(dc) min) for single-ended signals as well as the limitations for overshoot and undershoot.
2. Typ condition: typ model, 1.2 V, and 25 °C junction. Max condition: bcs model, 1.26V, and -40 °C. Min condition: wcs model, 1.14V, and Tj 125 °C.

Table 25. DDR3 mode DC Electrical characteristics

Symbol	Parameter	Test condition	Min	Typ	Max	Unit	Notes
Voh	High-level output voltage		0.8*ovdd			V	Note that the JEDEC JESD79_3E specification supersedes any specification in this document
Vol	Low-level output voltage	Iol= 1mA			0.2*ovdd	V	
Vref	Input reference voltage		0.49*ovdd	0.5*ovdd	0.51*ovdd	V	
Vih(dc)	DC input high voltage		Vref+0.1		ovdd	V	
Vil(dc)	DC input low voltage		ovss		Vref-0.1	V	
Vih(diff)	DC differential input logic high		0.2		Note[1]	V	
Vil(diff)	DC differential input logic low		Note[1]		-0.2	V	
Vtt[2]	Termination voltage	Vin = ovdd or 0	0.49*ovdd	0.5*ovdd	0.51*ovdd		
Iin[3]	Input current (no pullup/ pulldown)	Vi = 0 Vi = ovdd			3	uA	

Table continues on the next page...

Table 25. DDR3 mode DC Electrical characteristics (continued)

Symbol	Parameter	Test condition	Min	Typ	Max	Unit	Notes
Tri-state I/O supply current[3]	Icc-ovdd	Vin = ovdd or 0			5		
Tri-state vdd2p5 supply current[3]	Icc-vdd2p5	Vi = vddi or 0			1.5		
Tri-state core supply current[3]	Icc-vddi				1		
Driver unit (240 Ohm) calibration resolution	Rres				10	Ohm	

1. The single-ended signals need to be within the respective limits (Vih(dc) max, Vil(dc) min) for single-ended signals as well as the limitations for overshoot and undershoot.
2. Vtt is expected to track ovdd/2.
3. Typ condition: typ model, 1.5 V, and 25 °C. Max condition: bcs model, 1.575V, and -40 °C. Min condition: wcs model, 1.425V, and max Tj °C 125 °C junction

Table 26. LPDDR2 mode AC Electrical characteristics

Symbol	Parameter	Test condition	Min	Max	Unit	Notes
Vih(ac)	AC input logic high		Vref+0.22	ovdd	V	Note that the Jedec LPDDR2 specification (JESD209-2B) supersedes any specification in this document.
Vil(ac)	AC input logic low			Vref-0.22	V	
Vidh(ac)[1]	AC differential input high voltage		0.44	-	V	
Vidl(ac)[1]	AC differential input low voltage			0.44	V	
Vix(ac)[2]	AC differential input crosspoint voltage	Relative to ovdd/2	-0.12	0.12	V	
Vpeak	Over/undershoot peak			0.35	V	
Varea	Over/undershoot area (above ovdd or below ovss)	at 800MHz data rate		0.3	V*ns	
tsr	Single output slew rate		0.4	2	V/ns	
tskd	Skew between pad rise/fall asymmetry + skew cased by SSN			0.2	ns	

Table 31. 12-bit ADC Operating Conditions (continued)

Characteristic	Conditions	Symb	Min	Typ [1]	Max	Unit	Comment
Analog Source Resistance	12 bit mode f_{ADCK} = 40MHz ADLSMP=0, ADSTS=10, ADHSC=1	R_{AS}	-	-	1	kohms	T_{samp}=150 ns
R_{AS} depends on Sample Time Setting (ADLSMP, ADSTS) and ADC Power Mode (ADHSC, ADLPC). See charts for Minimum Sample Time vs R_{AS}							
ADC Conversion Clock Frequency	ADLPC=0, ADHSC=1 12 bit mode	f_{ADCK}	4	-	40	MHz	-
	ADLPC=0, ADHSC=0 12 bit mode		4	-	30	MHz	-
	ADLPC=1, ADHSC=0 12 bit mode		4	-	20	MHz	-

1. Typical values assume VDDAD = 3.3 V, Temp = 25°C, f_{ADCK}=20 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference

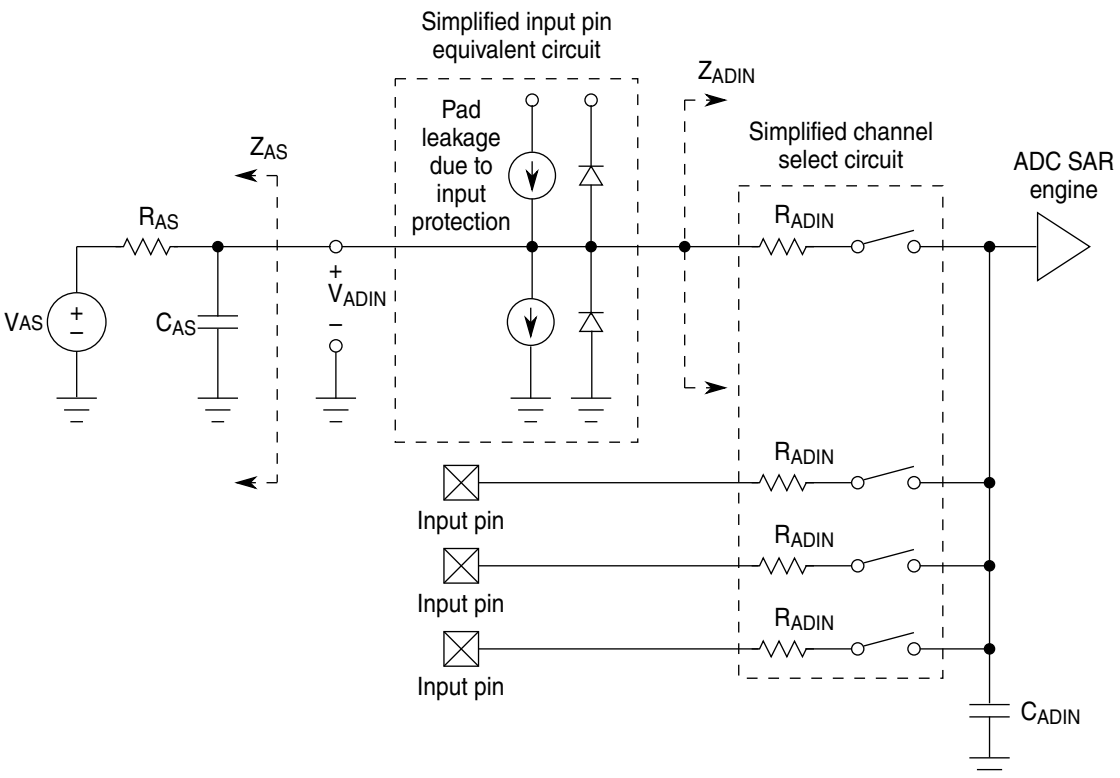

Figure 5. 12-bit ADC Input Impedance Equivalency Diagram

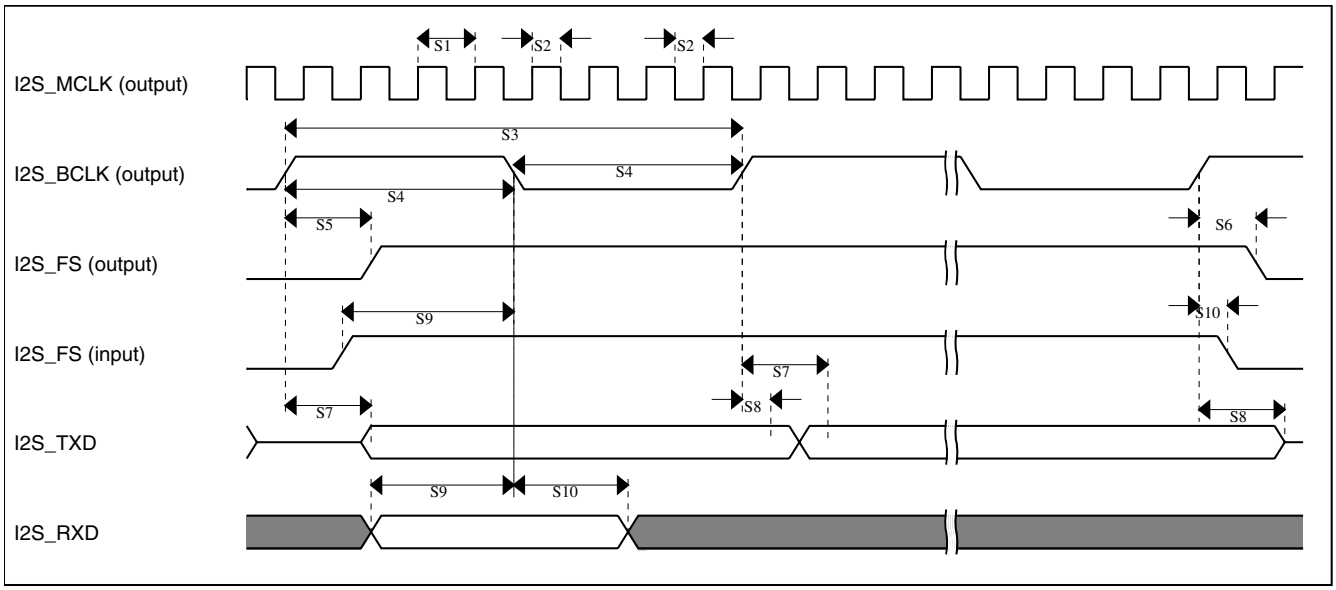

Figure 28. SAI Timing — Master Modes

Table 47. Slave Mode SAI Timing

Num	Characteristic	Min	Max	Unit
S11	SAI_BCLK cycle time (input)	4 x t_{SYS}	—	ns
S12	SAI_BCLK pulse width high/low (input)	40%	60%	BCLK period
S13	SAI_FS input setup before SAI_BCLK	10	—	ns
S14	SAI_FS input hold after SAI_BCLK	2	—	ns
S15	SAI_BCLK to SAI_TXD/SAI_FS output valid	—	20	ns
S16	SAI_BCLK to SAI_TXD/SAI_FS output invalid	0	—	ns
S17	SAI_RXD setup before SAI_BCLK	10	—	ns
S18	SAI_RXD hold after SAI_BCLK	2	—	ns

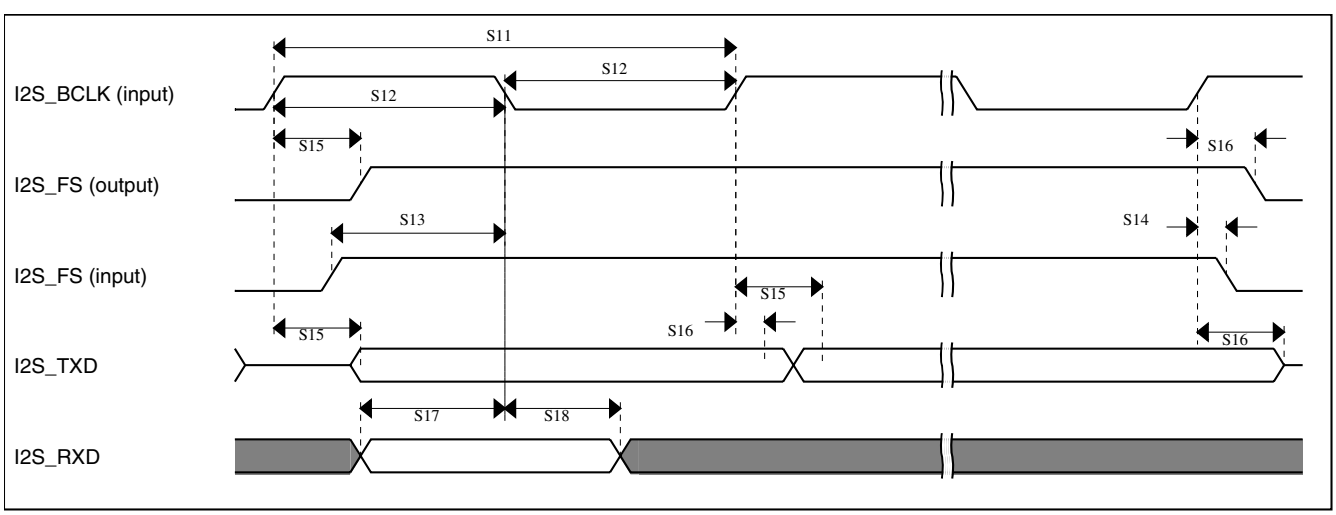

Figure 29. SAI Timing — Slave Modes

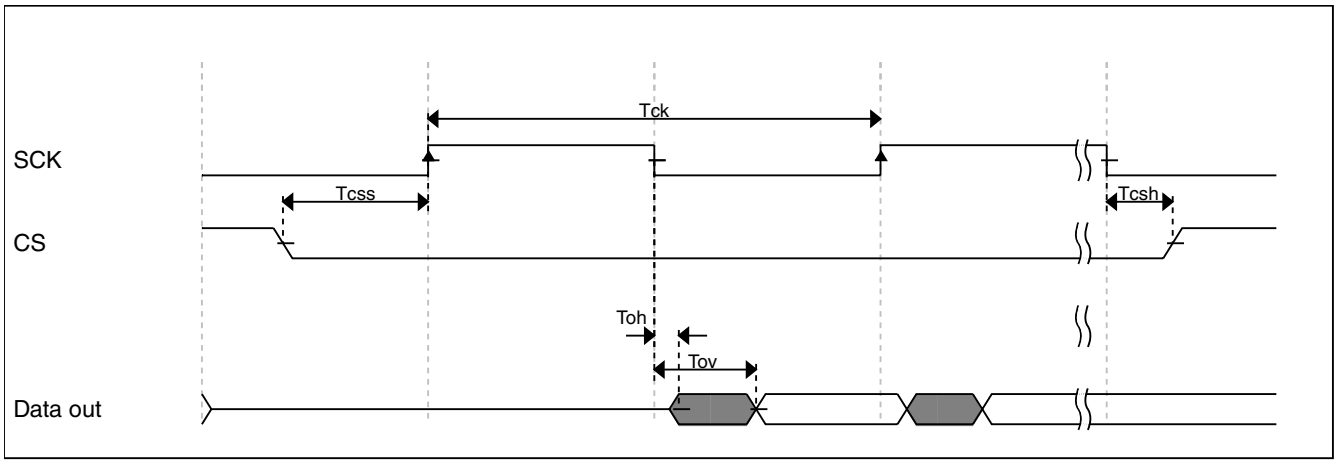

Figure 31. QuadSPI Output/Write timing (SDR mode)

Table 49. QuadSPI Output/Write timing (SDR mode)

Symbol	Parameter	Value		Unit
		Min	Max	
T_{ov}	Output Data Valid	-	3.2	ns
T_{oh}	Output Data Hold	0	-	ns
T_{ck}	SCK clock period	-	80	MHz
T_{css}	Chip select output setup time	3	-	SCK clock cycles
T_{csh}	Chip select output hold time	3	-	SCK clock cycles

NOTE

- Tcss and Tcsh are set by QuadSPI_FLSCH register, the minimum values of 3 shown are the register default values, refer to Reference Manual for further details.
- The timing in the datasheet is based on default values for the QuadSPI-SMPR register and is the recommended setting for highest SCK frequency in SDR mode.
- A negative time indicates the actual capture edge inside the device is earlier than clock appearing at pad.
- Frequency calculator guideline (Max read frequency): SCK > (Flash access time)max + (Tis)max
- A negative input hold time has no bearing on the maximum achievable operating frequency.

DDR Mode

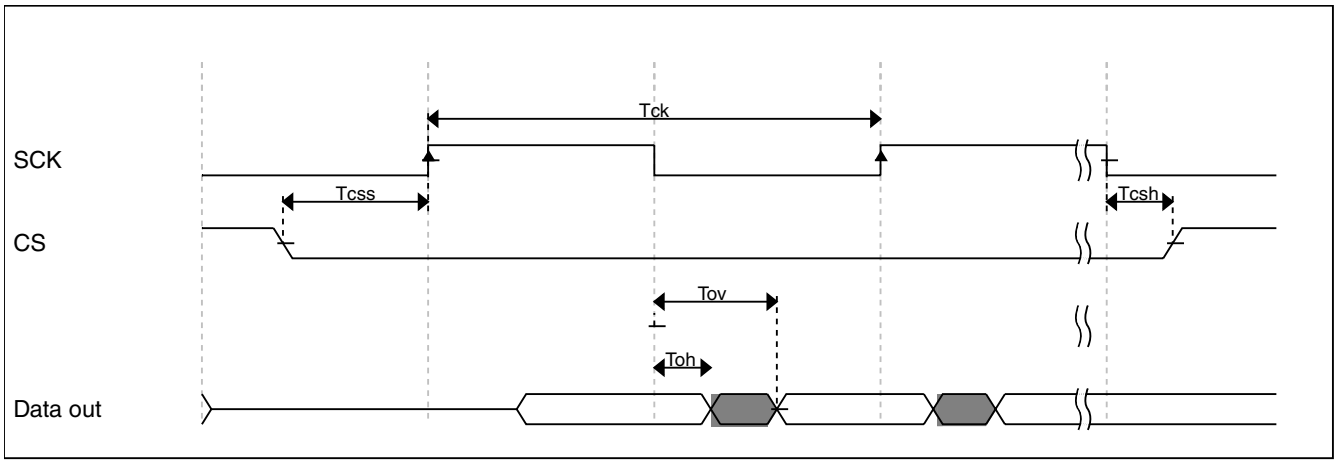

Figure 33. QuadSPI Output/Write timing (DDR mode)

Table 51. QuadSPI Output/Write timing (DDR mode)

Symbol	Parameter	Value		Unit
		Min	Max	
T_{ov}	Output Data Valid	—	3.2	ns
T_{oh}	Output Data Hold	0	—	ns
T_{ck}	SCK clock period	-	45	MHz
T_{css}	Chip select output setup time	3	-	Clk(sck)
T_{csh}	Chip select output hold time	3	-	Clk(sck)

9.5.2 NFC specifications

The NAND flash controller (NFC) implements the interface to standard NAND flash memory devices. This section describes the timing parameters of the NFC.

In the following table:

- T_H is the flash clock high time and
- T_L is flash clock low time,

which are defined as:

$T_{NFC} = T_H + T_L$

NOTE

Refer to the Reference Manual for further details on setting up the NFC clocks (CCM_CSCDR2[NFC_FRAC_DIV_EN + NFC_FRAC_DIV] and CCM_CSCDR3[NFC_PRE_DIV]).

9.5.4 DDR controller specifications

9.5.4.1 DDR3 Timing Parameters

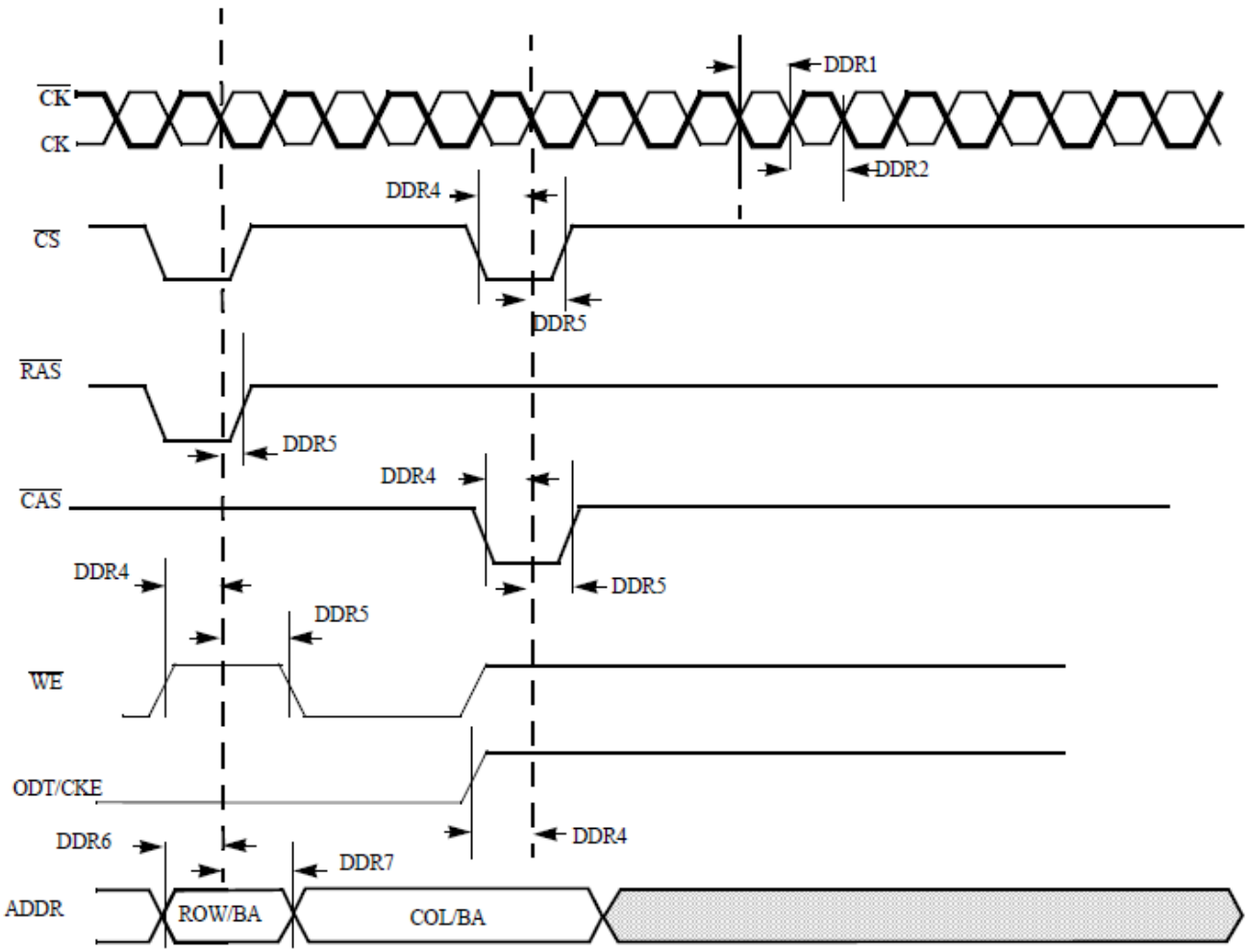

Figure 41. DDR3 Command and Address Timing Parameters

NOTE

RESET pin has a external weak pull DOWN requirement if DDR3 memory is NOT required to support content retention in the device low power modes where core voltage is off but DRAM voltage is on.

9.6 Communication interfaces

9.6.1 DSPI timing specifications

Table 60. DSPI timing

No.	Symbol	Characteristic	Condition	Min	Max	Unit
1	t_{SCK}	SCK Cycle Time	—	t_{SYS} * 2	—	ns
4	t_{SDC}	SCK Clock Pulse Width	—	40%	60%	t_{SCK}
2	t_{CSC}	CS to SCK Delay	Master	16	—	ns
3	t_{ASC}	After SCK Delay	Master	16	—	ns
5	t_A	Slave Access Time (SS active to SOUT driven)	Slave	—	15	ns
6	t_{DI}	Slave Disable Time (SS inactive to SOUT High-Z or invalid)	Slave	—	10	ns
9	t_{SUI}	Data Setup Time for Inputs	Master	9	—	ns
			Slave	4	—	
10	t_{HI}	Data Hold Time for Inputs	Master	0	—	ns
			Slave	2	—	
11	t_{DV}	Data Valid (after SCK edge) for Outputs	Master	—	5	ns
			Slave	—	10	
12	t_{HO}	Data Hold Time for Outputs	Master	0	—	ns
			Slave	0	—	

364 MAP BGA	176 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
V1	38	VDDA33_ ADC			VDDA33_ ADC							
V2	39	VSSA33_ ADC			VSSA33_ ADC							
U1	36	DACO0			DACO0							
U2	37	DACO1			DACO1							
Y4	—	VADCSE0			VADCSE0							
U4	—	VADCSE1			VADCSE1							
W4	—	VADCSE2			VADCSE2							
V5	—	VADCSE3			VADCSE3							
V3	—	VDDA33_ AFE			VDDA33_ AFE							
V4	—	VSSA33_AFE			VSSA33_AFE							
T5	—	VDD12_AFE			VDD12_AFE							
R5	—	VSS12_AFE			VSS12_AFE							
U5	—	VADC_AFE_ BANDGAP			VADC_AFE_ BANDGAP							
Y13	73	EXTAL			EXTAL							
W13	72	XTAL			XTAL							
Y12	70	EXTAL32			EXTAL32							
W12	71	XTAL32			XTAL32							
T4	35	RESETB/ RESET_OUT	RESETB/ RESET_OUT		RESETB/ RESET_OUT							
N5	19	PTA6		PTA6	RMII_ CLKOUT	RMII_CLKIN/ MII0_TXCLK		DCU1_ TCON11			DCU1_R2	
T3	34	TEST			TEST							
T1	30	Ext_POR			TEST2							
V12	69	DECAP_ V11_LDO_ OUT			DECAP_ V11_LDO_ OUT							
T11	65	DECAP_ V25_LDO_ OUT			DECAP_ V25_LDO_ OUT							
T2	33	BCTRL			BCTRL							
P5	31	VDDREG			VDDREG							
T12	68	VDD33_ LDOIN			VDD33_ LDOIN							
V11	67	VSS			VSS							
U11	66	VSS_KEL0			VSS_KEL0							
W14	—	LVDS0P			LVDS0P							
Y14	—	LVDS0N			LVDS0N							
K4	3	JTCLK/ SWCLK	JTCLK/ SWCLK	PTA8	JTCLK/ SWCLK			DCU0_R0			MLBCLK	

Table 75. RGPIO versus Pins (continued)

RGPIO	In GPIO module	Corresponding Pin on the chip	IOMUX register name	IOMUX register address
RGPIO[79]	PORT2[15]	PTD0	IOMUXC_PTD0	4004813C
RGPIO[80]	PORT2[16]	PTD1	IOMUXC_PTD1	40048140
RGPIO[81]	PORT2[17]	PTD2	IOMUXC_PTD2	40048144
RGPIO[82]	PORT2[18]	PTD3	IOMUXC_PTD3	40048148
RGPIO[83]	PORT2[19]	PTD4	IOMUXC_PTD4	4004814C
RGPIO[84]	PORT2[20]	PTD5	IOMUXC_PTD5	40048150
RGPIO[85]	PORT2[21]	PTD6	IOMUXC_PTD6	40048154
RGPIO[86]	PORT2[22]	PTD7	IOMUXC_PTD7	40048158
RGPIO[87]	PORT2[23]	PTD8	IOMUXC_PTD8	4004815C
RGPIO[88]	PORT2[24]	PTD9	IOMUXC_PTD9	40048160
RGPIO[89]	PORT2[25]	PTD10	IOMUXC_PTD10	40048164
RGPIO[90]	PORT2[26]	PTD11	IOMUXC_PTD11	40048168
RGPIO[91]	PORT2[27]	PTD12	IOMUXC_PTD12	4004816C
RGPIO[92]	PORT2[28]	PTD13	IOMUXC_PTD13	40048170
RGPIO[93]	PORT2[29]	PTB23	IOMUXC_PTB23	40048174
RGPIO[94]	PORT2[30]	PTB24	IOMUXC_PTB24	40048178
RGPIO[95]	PORT2[31]	PTB25	IOMUXC_PTB25	4004817C
RGPIO[96]	PORT3[0]	PTB26	IOMUXC_PTB26	40048180
RGPIO[97]	PORT3[1]	PTB27	IOMUXC_PTB27	40048184
RGPIO[98]	PORT3[2]	PTB28	IOMUXC_PTB28	40048188
RGPIO[99]	PORT3[3]	PTC26	IOMUXC_PTC26	4004818C
RGPIO[100]	PORT3[4]	PTC27	IOMUXC_PTC27	40048190
RGPIO[101]	PORT3[5]	PTC28	IOMUXC_PTC28	40048194
RGPIO[102]	PORT3[6]	PTC29	IOMUXC_PTC29	40048198
RGPIO[103]	PORT3[7]	PTC30	IOMUXC_PTC30	4004819C
RGPIO[104]	PORT3[8]	PTC31	IOMUXC_PTC31	400481A0
RGPIO[105]	PORT3[9]	PTE0	IOMUXC_PTE0	400481A4
RGPIO[106]	PORT3[10]	PTE1	IOMUXC_PTE1	400481A8
RGPIO[107]	PORT3[11]	PTE2	IOMUXC_PTE2	400481AC
RGPIO[108]	PORT3[12]	PTE3	IOMUXC_PTE3	400481B0
RGPIO[109]	PORT3[13]	PTE4	IOMUXC_PTE4	400481B4
RGPIO[110]	PORT3[14]	PTE5	IOMUXC_PTE5	400481B8
RGPIO[111]	PORT3[15]	PTE6	IOMUXC_PTE6	400481BC
RGPIO[112]	PORT3[16]	PTE7	IOMUXC_PTE7	400481C0
RGPIO[113]	PORT3[17]	PTE8	IOMUXC_PTE8	400481C4
RGPIO[114]	PORT3[18]	PTE9	IOMUXC_PTE9	400481C8
RGPIO[115]	PORT3[19]	PTE10	IOMUXC_PTE10	400481CC
RGPIO[116]	PORT3[20]	PTE11	IOMUXC_PTE11	400481D0
RGPIO[117]	PORT3[21]	PTE12	IOMUXC_PTE12	400481D4

Table continues on the next page...

Table 79. Revision History (continued)

Rev. No.	Date	Substantial Changes
		Updated Power supply diagram Updated AC electrical specification of following modules: DCU, 12-bit DAC, Ethernet, Enhanced Serial Audio Interface (ESAI), SAI/I2S, Flexbus, MLB, DSPI, 24MHz External Oscillator, JTAG, Debug, ESAI, QSPI Updated Thermal Attributes for 364 MAPBGA Updated Freescale document number for 176-pin LQFP and 364 MAPBGA Updated VREG specifications Added WBREG specifications Updated Recommended operating conditions table Updated DAC INL and DNL charts Updated Pinouts
Rev 4.1	12/2012	Editorial updates: Removed instances of VF7xx and VF4xx.
Rev 5	April 2013	• Removed references to VF1xxR and refernces to F100 and 144 LQFP and 256 MAPBGA • Replaced references to Auto and IMM by R-series and F-series respectively • In the feature list, the ARM Core frequency changed to 500 MHz for F-series • In the feature list, changed the DRAM controller frequency • Updated Part Nummbering format • Clarified the Fields table as per Marketing • Sample numbers updated • From the VREG electrical specifications tables, deleted pre-trimming rows and comments • .In the HPREG electrical characteristics table, add footnote on maximum Output Current Capacity • In the ULPREG electrical characteristics table, clarified max value of Output voltage @ no load and min value of Output voltage @ full load • In the WBREG electrical characteristics table, clarified max value of Output voltage @ no load and min value of Output voltage @ full load

Table continues on the next page...

Table 79. Revision History (continued)

Rev. No.	Date	Substantial Changes
Rev 6	Jan 2014	• Added QuadSPI electricals • Changed VBB references to VBAT • In the feature list, clarified that ECC supported for 8-bit mode only, not 16-bit. • Revised the part number format • Revised the field table • Added Absolute Maximum Rating table, which was madde non_cust in the previous version • In the Power Consumption Operating Behavior table, Revised min and max value of IDD_LPS3 and IDD_LPS2. Removed IDD_LPS1 row • In the USB PHY Current Consumption table, removed the Normal Mode • In the Power Sequence table, revised the Power UP/ Down Order column for USB0_VBUs and USB1_VBUS • In the Recommended operating conditions table, revised the min value of VBAT. Revised the min value of VREFH_ADC Revised the min and max values of SDRAMC_VDD1P5 • In the Recommended Connections for Unused Analog Interfaces section, added the notes. Revised the Recommendation if Unused column • In the 12-bit ADC operating conditions, revised Conditions for Ground voltage. Revised min Ref High Voltage • In the 12-bit DAC operating requirements, revised the min and max value of VREFH_ADC • In the SDHC switching specifications, revised the max value of SD6 • In the 24MHz external oscillator electrical characteristics table, revised the min value of VIH and max value of VIL
Rev 7	April 2014	• Updated Note in "Power supply" section. • Updated Absolute maximum ratings section: solute maximum ratings Table - FA_VDD row: Min and Max column • Updated figure "12-bit ADC Input Impedance Equivalency Diagram"

Table continues on the next page...